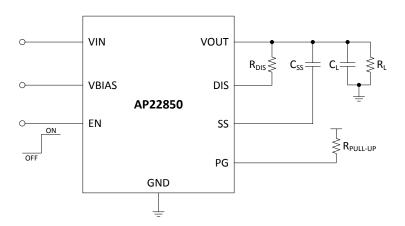


Typical Applications Circuit

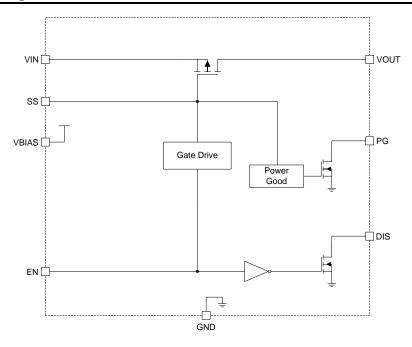


Pin Descriptions

Pin Name	Pin Number	Function
SS 1		Soft-Start Adjust An external capacitor connected between this pin and VOUT sets the ramp-up time of VOUT
EN 2 Enable Input Active high		'
VIN	3, 4	Input Voltage Connects to the Source of the P-channel MOSFET
GND	5	Ground
VRIAS		Supply Voltage Recommended range: 2.5V ≤ VBIAS ≤ 5.5V
PG 7 Power Good Open-drain output to indicate w		Power Good Open-drain output to indicate when the P-channel pass switch is fully enhanced
DIS Output Discharge An external resistor between DIS and VOUT sets the discharge rate of VOUT		i g
VOUT PAD Output Voltage PAD connects to the Drain of the P-channel		Output Voltage PAD connects to the Drain of the P-channel MOSFET



Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.) (Note 4)

Symbol	Parameter	Ratings	Units	
V _{IN}	Input Voltage		12.0	V
V _{OUT}	Output Voltage		12.0	V
V _{EN}	Enable Voltage		6.0	V
V _{BIAS}	Bias Voltage		6.0	V
IL	Load Current	8.0	А	
T _{J(max)}	Maximum Junction Temperature	125	°C	
T _{ST}	Storage Temperature		−55 to +150	°C
	Davies Discinction	(Note 5)	0.35	W
P _D	Power Dissipation	(Note 6)	1.8	W
-	The second Decision on the Australia	(Note 5)	300	2011
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 6)	60	°C/W
R ₀ JC	Thermal Resistance, Junction to Case	-	5	°C/W

Notes:

- 4. Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.
- 5. For a device surface mounted on minimum recommended pad layout, in still air conditions; the device is measured when operating in a steady state condition.
- 6. For a device surface mounted on 25mm by 25mm by 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady state condition.



Recommended Operating Conditions (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Units
V _{IN}	Input Voltage	4.5	11.0	V
V_{BIAS}	Bias Voltage	2.5	5.5	V
V _{EN}	Enable Voltage	0	5.5	V
V_{PG}	Power Good Voltage Range	0	11.0	V
T _A	Operating Ambient Temperature	-40	+85	°C

$\hline \textbf{Electrical Characteristics} \ \ (@T_A = +25^{\circ}C, \ \ V_{BIAS} = 2.5V - 5.5V, \ C_{IN} = 1 \mu F, \ C_L = 100 nF, \ unless \ otherwise \ specified.)$

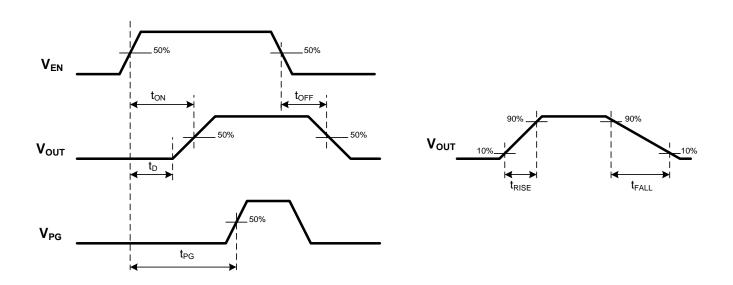
Symbol	Parameters	Condition	ns	Min	Тур	Max	Unit
			V _{IN} = 10.0V	-	5.0	200	
I_{VIN_Q}	V _{IN} Quiescent Current	I _{OUT} = 0A	$V_{IN} = 8.4V$	-	3.0	200	nA
			$V_{IN} = 5.0V$	-	1.0	200	
I _{VBIAS_Q}	V _{BIAS} Quiescent Current	V _{IN} = 12.0V, I _{OUT} = 0A		-	1.0	200	nA
I _{VIN_SD}	V _{IN} Shutdown Current	V _{IN} = 12.0V, V _{EN} = 0V		-	2.0	200	nA
I _{VBIAS_SD}	V _{BIAS} Shutdown Current	V _{IN} = 12.0V, V _{EN} = 0V		-	2.0	200	nA
	Load Switch On-Resistance	I _{OUT} = −1A	V _{IN} = 10.0V	-	21	31	
R _{DS(ON)}			V _{IN} = 8.4V	-	21	31	mΩ
			$V_{IN} = 5.0V$	-	23	33	
$V_{\text{IH_EN}}$	EN Input Logic High Voltage	-		1.0	-	-	V
$V_{IL_{_}EN}$	EN Input Logic Low Voltage	-		-	-	0.5	V
I _{LEAK_EN}	EN Input Leakage	V _{EN} = V _{BIAS}		-	-	100	nA
D	Discharge FFT On Begintage)/ 0)/ l 40m/	V _{BIAS} = 5.0V	-	8	11	Ω
R _{DS_DIS}	Discharge FET On-Resistance	$V_{EN} = 0V$, $I_{DIS} = 10mA$	$V_{BIAS} = 2.5V$	-	11	16	Ω
V_{OL_PG}	Power Good Output Low Level	I _{OL_PG} = 100μA, V _{EN} = 0V		-	-	0.2	V
I _{OZ_PG}	Power Good High-Impedance Current	V _{PG} = V _{BIAS} , V _{EN} = V _{BIAS}		-	-	0.05	μΑ



Switching Characteristics (@ $T_A = +25^{\circ}C$, $V_{BIAS} = 2.5V - 5.5V$, $C_{IN} = 1\mu F$, $C_L = 100nF$, unless otherwise specified)

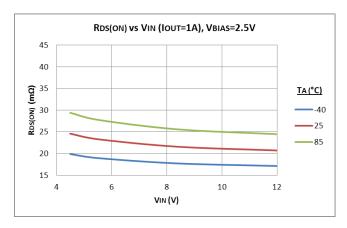
Symbol	Parameters	Conditions	3	Min	Тур	Max	Unit
			V _{IN} = 10.0V		100		
t _{RISE}	Output Rise Time	$R_L=10\Omega,C_{SS}=10nF$	V _{IN} = 8.4V	-	102	-	μs
			V _{IN} = 5.0V		104		
			V _{IN} = 10.0V		70		
t _{ON}	Output Turn-ON Delay Time	$R_L=10\Omega,C_{SS}=10nF$	$V_{IN} = 8.4V$	-	75	-	μs
			$V_{IN} = 5.0V$		82		
tFALL	Output Fall Time	$R_L = Open, R_{DIS} = 240\Omega,$ $C_{SS} = 10nF$	V _{IN} = 10.0V		70		
			$V_{IN} = 8.4V$	-	71	-	μs
			V _{IN} = 5.0V		75		
		R_L = Open, R_{DIS} = 240 Ω , C_{SS} = 10nF	V _{IN} = 10.0V		41		μs
t _{OFF}	Output Turn-OFF Delay Time		$V_{IN} = 8.4V$	-	45	-	
			$V_{IN} = 5.0V$		60		
			V _{IN} = 10.0V		12		
t_D	Output Start Delay Time	$R_L = 10\Omega$, $C_{SS} = 10nF$	$V_{IN} = 8.4V$	-	16	-	μs
			$V_{IN} = 5.0V$		22		
			V _{IN} = 10.0V		250		
t_{PG}	Power Good Delay Time	$R_L = 10\Omega$, $C_{SS} = 10nF$	V _{IN} = 8.4V	-	230	-	μs
			V _{IN} = 5.0V		205		

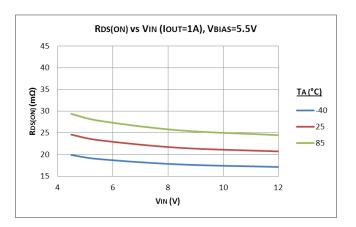
ton/toff Waveforms

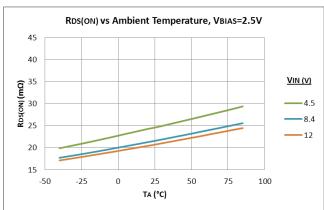


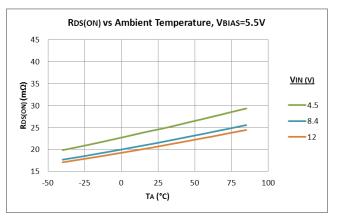


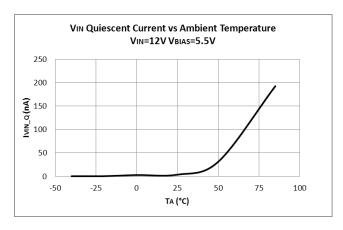
Typical Performance Characteristics (@T_A = +25°C, VBIAS = 5V, unless otherwise specified.)

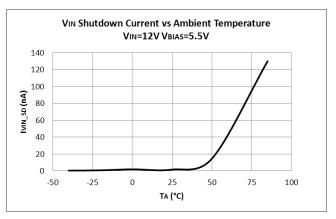


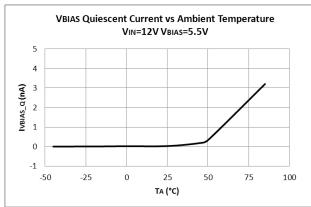


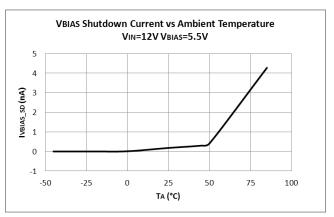






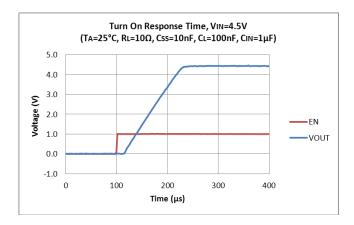


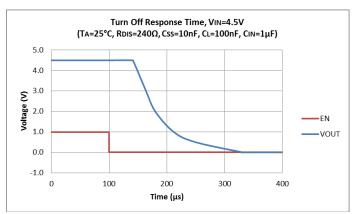


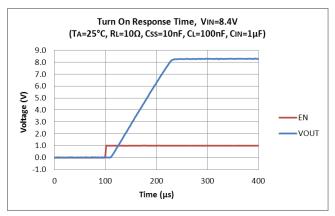


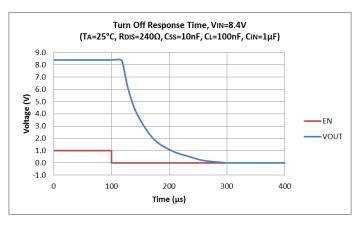


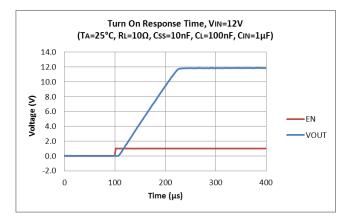
Typical Performance Characteristics (cont.) (@T_A = +25°C, VBIAS = 5V, unless otherwise specified.)

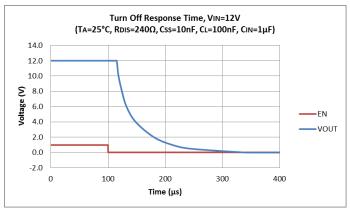






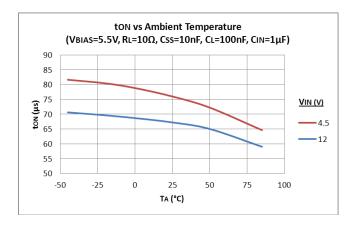


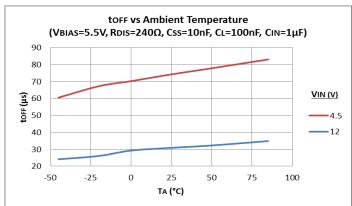


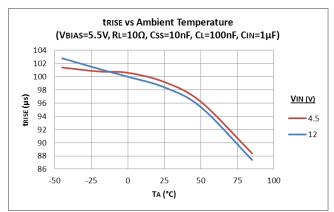


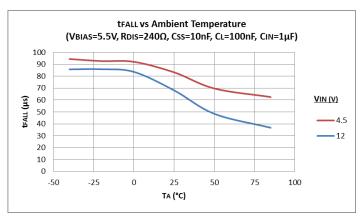


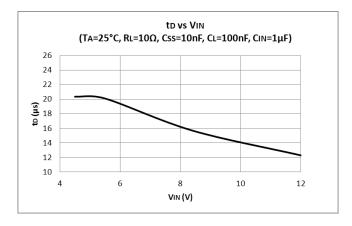
Typical Performance Characteristics (cont.) (@T_A = +25°C, VBIAS = 5V, unless otherwise specified.)













Application Information

Theory of Operation

The AP22850 is a load switch that can be used to isolate or power-down part of a system in order to reduce power consumption, particularly in battery-powered devices. The PMOS pass element in AP22850 is turned on when the EN pin is pulled high. This provides a controlled current source to decrease the voltage on the SS pin to GND, effectively turning on the PMOS pass switch and connecting VOUT to VIN.

During the turn-on phase, once the SS voltage reaches close to GND, the PMOS pass switch is fully enhanced with maximum available overdrive. Power is deemed to be good and the Power Good (PG) output is pulled high via an external pull-up resistor. The rise-time on VOUT is controlled by the value of the external capacitor between the SS and VOUT pin.

When EN is pulled low, the switch turns off and isolates VOUT from VIN. In addition, PG is pulled to indicate that the power is no longer good. The discharge pin keeps VOUT grounded while EN is low. The fall time on VOUT is largely controlled by the value of the discharge resistor and the capacitance on the output.

Input and Output Voltage

The Input Voltage (VIN) should be between 4.5V and 11V. With the switch is activated, the Output Voltage (VOUT) will be the input voltage minus the voltage drop across the device.

Enable

The GPIO compatible EN input allows the output current to be switched on and off. A high signal (switch on) should be at least 1V, and the low signal (switch off) no higher than 0.5V.

This pin should not be left floating. It is advisable to hold EN low when applying or removing power.

VBIAS

The VBIAS input provides a positive power supply to the controller circuitry. It should be set in the range of 2.5V to 5.5V. VBIAS signal is essential for the device to power up and should be set before the switch is enabled.

Power Good

Power Good is an open-drain output that indicates when the pass switch is enhanced enough to deliver current to the load. PG is high (open-drain high impedance) when power is deemed good, and low when the power is deemed to not be good.

PG can be pulled up to any voltage to a maximum of 11V, although it is recommended to pull it up to VOUT with a resistor greater than $20k\Omega$. The advantage of pulling up PG to VOUT is that when EN is low, VOUT is also grounded. Thus, no power is wasted in the pull-up resistor.

If this feature is not required, then PG pin can be left floating

Input and Output Capacitors

AP22850 does not require any capacitor on VIN for successful operation. In addition, this device has no input-to-output capacitor ratio stipulation to account for current through the body diode. However, to minimize voltage dip on VIN due to inrush current at start-up, a capacitor can be place on VIN.

For heavier loads, it is recommended that the VIN and VOUT trace lengths be kept to a minimum. In addition, a bulk capacitor (≥ 10µF) may also be placed close to the VOUT pin. If using a bulk capacitor on VOUT, it is important to control the inrush current by choosing an appropriate soft-start time in order to minimize the droop on the input supply.



Application Information (cont.)

Adjustable Slew Rate/Soft-Start

SS pin allows the output ramp time of the switch to be controlled using an external capacitor (C_{SS}). This timing capacitor is connected between the SS and VOUT pin. Rise times (in μ s) for different values of C_{SS} and V_{IN} are shown in the table below with $V_{BIAS} = 5.5V$.

Measured at +2	Rise Time (in μ s) Measured at +25°C using 0805 X7R 10% 50V capacitors, C_L = 100nF, R_{DIS} = 1K, R_L = 10 Ω							
V _{IN} C _{SS}	4.5V	7.0V	9.0V	11.0V				
1nF	13.6	12.4	12.0	11.4				
10nF	97.2	99.2	98.8	97.9				
100nF	955	1,075	1,154	1253				

Table 1 Timing Capacitors and Rise Times

Adjustable Discharge

When EN goes low, VOUT is discharged to ground through the discharge resistor (R_{DIS}) on the DIS pin. A value greater than 240 Ω is recommended for R_{DIS} .

While the discharge/fall-time on VOUT can be controlled using R_{DIS} , capacitors on VOUT and SS also contribute to the timing. Higher discharge resistance increases the RC time constant and hence, the discharge time. Fall times (in μ s) for different values of R_{DIS} and V_{IN} are shown in the table below with $V_{BIAS} = 5.5V$.

1,206 250mW 1% Discharge resistor (Ω)	Fall Time (in μ s) Measured at +25°C, C _L = 100nF, C _{SS} = 1nF, R _L = open		
	5V	11V	
240	71.8	69.5	
1,000	264.2	276.7	
3,900	1,029	1,078	

Table 2 Discharge Resistors and Output Voltage Fall Time

March 2015



Board Layout and Thermal Considerations

Due to the high current capacity of the load switch, PCB layout needs to ensure good thermal distribution during operation. The top and bottom of AP22850EV1, (the evaluation board for AP22850), can be seen below.

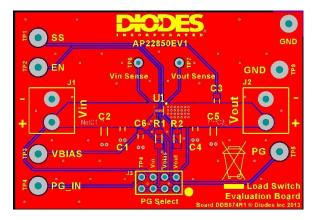


Figure 3 PCB Copper Layout & Silk Screen - Top

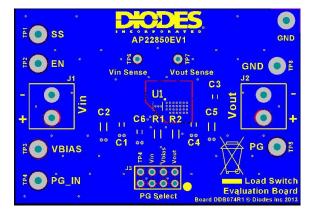


Figure 4 PCB Copper Layout & Silk Screen - Bottom

Thermal vias are used directly underneath the chip to help distribute the heat from the device. The ground plane on the underside of the board effectively acts as a large heatsink. The widths of the tracks carrying VIN and VOUT are kept wide. Vias are also distributed around the board to aid thermal conduction and to ensure a consistent potential, particularly around the ground connections of the capacitors. All capacitors used are located as close as possible to the AP22850 to minimize any parasitic effects.

The maximum junction temperature of the AP22850 is +125°C. To ensure that this is not exceeded, the following equation can be used to give an approximation of junction temperature. Temperature readings taken with a thermal camera can also give a good approximation of power dissipation with the use of this equation. The board layout has a major influence on the parameter θ_{IA} .

$$T_I = T_A + (\theta_{IA} \times P_D)$$

Where, T_I = Junction Temperature (°C)

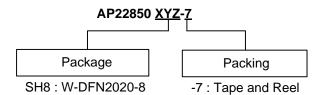
 T_A = Ambient Temperature (°C)

 θ_{IA} = Junction to Ambient Thermal Impedance (°C/W)

 P_D = Power Dissipation (voltage drop across device × output current) (W)



Ordering Information



Part Number	Package	Packaging	7" Tape a	and Reel
Part Number	Code	(Note 7)	Quantity	Part Number Suffix
AP22850SH8-7	SH8	W-DFN2020-8	3,000/Tape & Reel	-7

Note:

7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Marking Information

W-DFN2020-8

(Top View)

 XX: Identification code

Y: Year 0~9

 \underline{W} : Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents 52 and 53 week

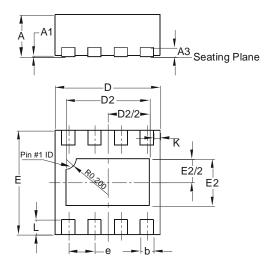
X: A~Z: Internal Code

Device	Package	Identification Code	
AP22850SH8-7	W-DFN2020-8	WC	



Package Outline Dimensions (All dimensions in mm)

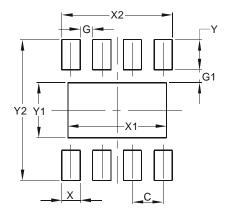
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	W-DFN2020-8 Type C							
Dim Min Max Ty								
Α	0.770	0.830	0.800					
A1	0	0.05	0.02					
А3	-	-	0.152					
b	0.20	0.30	0.25					
D	1.950	2.075	2.000					
D2	1.50	1.70	1.60					
E	1.950	2.075	2.000					
E2	0.80	1.00	0.90					
е	-	-	0.50					
K	-	-	0.125					
L	0.240	0.340	0.290					
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.500
G	0.200
G1	0.210
Х	0.300
X1	1.600
X2	1.750
Y	0.490
Y1	0.900
Y2	2.300



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